



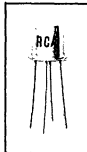
RF Power Transistors

2N918
2N3600

RCA-2N918 and RCA-2N3600 are double-diffused epitaxial planar transistors of the silicon n-p-n type. They are extremely useful in low-noise-amplifier, oscillator, and converter applications at VHF frequencies.

These devices utilize a hermetically sealed four-lead JEDEC TO-72 package. All active elements of the transistor are insulated from the case, which may be grounded by means of the fourth lead in applications requiring minimum feedback capacitance, shielding of the device, or both.

SILICON N-P-N EPITAXIAL PLANAR TRANSISTORS



JEDEC TO-72

For VHF Applications
In Military, Communications,
and Industrial Equipment

MAXIMUM RATINGS, Absolute-Maximum Values:

2N918 2N3600

COLLECTOR-TO-BASE VOLTAGE, V_{CB0}	30	30 max.	V
COLLECTOR-TO-EMITTER VOLTAGE, V_{CE0}	15	15 max.	V
EMITTER-TO-BASE VOLTAGE, V_{EB0}	3	3 max.	V
COLLECTOR CURRENT, I_C	50	* max.	mA

TRANSISTOR DISSIPATION, P_T :

For operation with heat sink:

At case temperatures**	<table border="1"> <tr> <td>up to 25°C</td> <td>300</td> <td>300 max.</td> <td>mW</td> </tr> <tr> <td>above 25°C</td> <td colspan="3">Derate at 1.71 mW/°C</td> </tr> </table>	up to 25°C	300	300 max.	mW	above 25°C	Derate at 1.71 mW/°C		
up to 25°C	300	300 max.	mW						
above 25°C	Derate at 1.71 mW/°C								

For operation at ambient temperatures:

At ambient temperatures	<table border="1"> <tr> <td>up to 25°C</td> <td>200</td> <td>200 max.</td> <td>mW</td> </tr> <tr> <td>above 25°C</td> <td colspan="3">Derate at 1.14 mW/°C</td> </tr> </table>	up to 25°C	200	200 max.	mW	above 25°C	Derate at 1.14 mW/°C		
up to 25°C	200	200 max.	mW						
above 25°C	Derate at 1.14 mW/°C								

TEMPERATURE RANGE:

Storage and Operating (Junction)	-65 to +200	°C
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LEAD TEMPERATURE (During Soldering):

At distances \geq 1/16 inch from seating surface for 60 seconds max.	300	300 max.	°C
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* Limited by transistor dissipation.
** Measured at center of seating surface.

FEATURES

- high gain-bandwidth product
 - hermetically sealed four-lead package
 - low leakage current
 - high 200-MHz power gain
- 2N3600
- low noise figure
NF = 4.5 dB max. at 200 MHz
 - low collector-to-base time constant
 $r_b' C_c = 15$ ps max.
 - high power gain as neutralized amplifier
 $G_{pe} = 17$ dB min. at 200 MHz

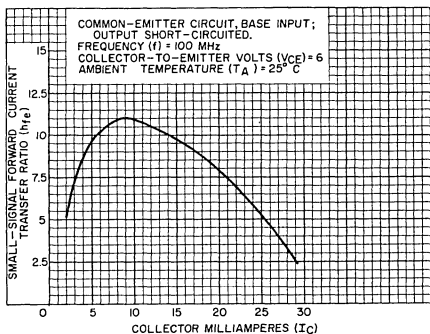
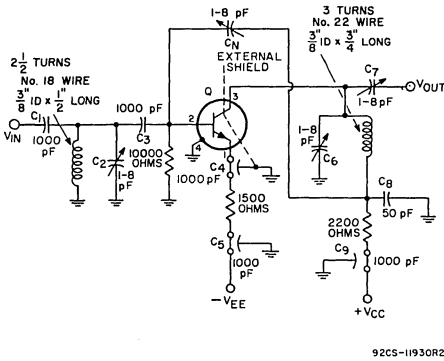


Fig. 1 - Small-signal beta characteristic for types 2N918 and 2N3600.

ELECTRICAL CHARACTERISTICS

Characteristics	Symbols	TEST CONDITIONS							LIMITS						Units	
		Ambient Temperature	Frequency	DC Collector-to-Base Voltage	DC Collector-to-Emitter Voltage	DC Emitter Current	DC Collector Current	DC Base Current	Type 2N918			Type 2N3600				
				V _{CB}	V _{CE}	I _E	I _C	I _B	Min.	Typ.	Max.	Min.	Typ.	Max.		
		T _A	f	V	V	mA	mA	mA								
		°C	MHz	V	V	mA	mA	mA	Min.	Typ.	Max.	Min.	Typ.	Max.		
Collector-Cutoff Current	I _{CBO}	25 150		15 15		0 0			-	-	0.01 1	-	-	0.01 1	μA μA	
Collector-to-Base Breakdown Voltage	BV _{CB0}	25				0	0.001		30	-	-	30	-	-	V	
Collector-to-Emitter Sustaining Voltage	BV _{CE0(sus)}	25					3	0	15	-	-	15	-	-	V	
Emitter-to-Base Breakdown Voltage	BV _{EB0}	25				0.01	0		3	-	-	3	-	-	V	
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	25					10	1	-	-	0.4	-	-	0.4	V	
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	25					10	1	-	-	1	-	-	1	V	
Static Forward Current-Transfer Ratio	h _{FE}	25			1		3		20	-	-	20	-	150		
Small-Signal Forward Current-Transfer Ratio ^a	h _{fe}	25	100 100 1 kHz		10 6 6		4 5 2		6	-	-	-	-	8.5 40 200	-	15 200
Common-Base Output Capacitance ^b	C _{ob}	25	0.1 to 1	10 0		0 0			-	-	1.7 3	-	-	-	pF pF	
Collector-to-Base Feedback Capacitance ^b	C _{cb}	25	0.1 to 1	10		0			-	-	-	-	-	1	pF	
Common-Base Input Capacitance ^c (V _{EB} = 0.5V)	C _{ib}	25	0.1 to 1				0		-	-	2	-	1.4	-	pF	
Collector-to-Base Time Constant ^a	t _b 'C _c	25	40 31.9	6 6			2 5		-	15	-	-	4	-	ps ps	
Small-Signal Power Gain in Neutralized Common-Emitter Amplifier Circuit ^a (See Fig.2 & Fig.3)	G _{pe}	25	200		12 6		6 5		15	21	-	-	17	-	24	dB dB
Small-Signal Power Gain in Unneutralized Common-Emitter Amplifier Circuit ^a (See Fig.4)	G _{pe}	25	200		10		5		-	13	-	-	-	-	-	dB
Power Output in Common-Emitter Oscillator Circuit ^a (See Fig.5)	P _o	25	≥ 500	10		12			30	-	-	20	-	-	-	mW
Nose Figure ^a (See Fig.2)	NF	25	200		6		1.5		-	-	-	-	-	-	4.5	dB
Noise Figure ^{a,d}	NF	25	60		6		1		-	-	6	-	-	-	3	dB

^a Lead No.4 (case) grounded.^b Three-terminal measurement of the collector-to-base capacitance with the case and emitter leads connected to the guard terminal.^c Lead No.4 (case) floating.^d Generator Resistance (R_g) = 400 ohms.

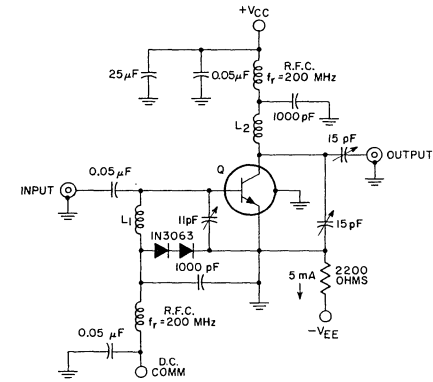


92CS-11930R2

NOTE: (Neutralization Procedure): (a) Connect a 50- Ω rf voltmeter to the output of a 200-MHz signal generator ($R_g = 50 \Omega$), and adjust the generator output to 5 mV. (b) Connect the generator to the input and the rf voltmeter to the output of the amplifier, as shown above. (c) Apply V_{EE} and V_{CC} , and adjust the generator output to provide an amplifier output of 5 mV. (d) Tune C_2 , C_6 , and C_7 for maximum amplifier output, readjusting the generator output, as required, to maintain an output of 5 mV from the amplifier. (e) Interchange the connections to the signal generator and the rf voltmeter. (f) With sufficient signal applied to the output terminals of the amplifier, adjust CN for a minimum indication at the amplifier input. (g) Repeat steps (a), (b), (c), and (d) to determine if retuning is necessary.

Q = Type 2N3600

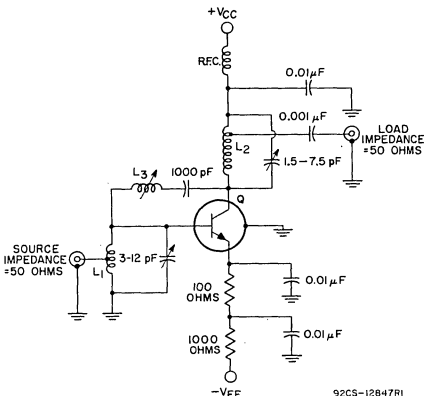
Fig. 2 - Neutralized amplifier circuit used to measure power gain and noise figure at 200 MHz for type 2N3600.



92CS-12848R1

L_1 - 1 loop #12 AWG wire; $I_D = 13/16"$
 L_2 - 1/2 loop #12 AWG wire; $I_D = 1-3/16"$
 Q = 2N918

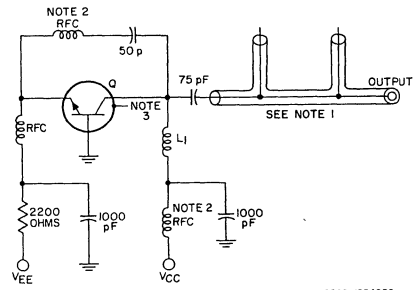
Fig. 4 - Circuit used to measure 200-MHz unneutralized power gain for type 2N918.



92CS-12847R1

L_1 - 3.5 turns No.16 tinned copper wire; 5/16" dia.; 7/16" long; turns ratio $\approx 4:2$
 L_2 - 8 turns No.16 tinned copper wire; 1/8" dia.; 7/8" long; turns ratio $\approx 8:1$
 L_3 - MILLER #4303 (0.4 - 0.65 μ H) or equivalent
 Q = Type 2N918

Fig. 3 - Neutralized amplifier circuit used to measure power gain at 200 MHz for type 2N918.



92CS-12849R2

Note 1 - Coaxial-Line output network consisting of:
 2 General Radio Type 874 TEE or equivalent
 1 General Radio Type 874-D20 Adjustable Stub or equivalent
 1 General Radio Type 874-LA Adjustable Line or equivalent
 1 General Radio Type 874-WN3 Short-circuit termination or equivalent
 Note 2 - RFC = 0.2 μ H Ohmite #2-460 or equivalent
 Note 3 - Lead Number 4 (case) floating
 L_1 - 2 turns #16AWG wire, 3/8 inch OD, 1-1/4 inch long
 Q = 2N918 or 2N3600

Fig. 5 - Circuit used to measure 500-MHz oscillator power output for types 2N918 and 2N3600.

TWO-PORT ADMITTANCE (y) PARAMETERS AS FUNCTIONS OF COLLECTOR CURRENT (I_C) FOR RCA TYPES 2N918 AND 2N3600

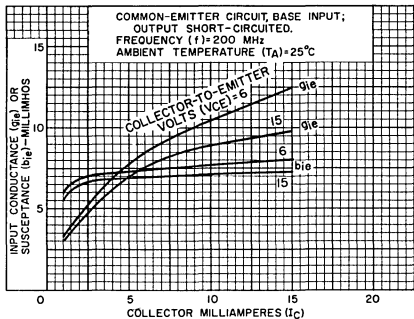


Fig. 6 - Input admittance (y_{ie}).

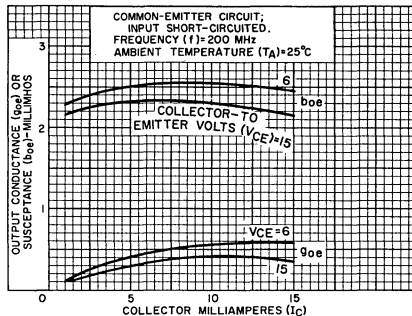


Fig. 7 - Output admittance (y_{oe}).

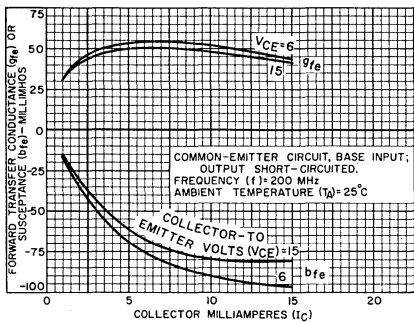


Fig. 8 - Forward transadmittance (y_{fe}).

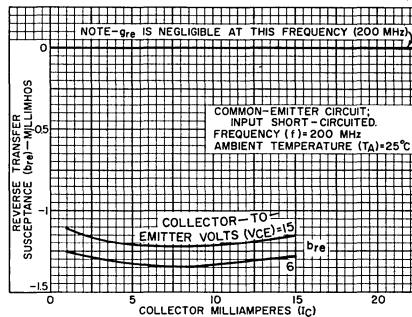


Fig. 9 - Reverse transadmittance (y_{re}).

TERMINAL CONNECTIONS

- LEAD 1 - EMITTER
- LEAD 2 - BASE
- LEAD 3 - COLLECTOR
- LEAD 4 - CONNECTED TO CASE